

TMBAT 49

SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching. This device has integrated protection against excessive voltage such as electrostatic discharges.



ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	80	V
١ _F	Forward Continuous Current	500	mA
I _{FRM}	Repetitive Peak Forward Current	3	A
I _{FSM}	Surge non Repetitive Forward Current	10	А
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	°C ℃
TL	Maximum Temperature for Soldering during	260	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-leads	110	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
I _R *	$T_j = 25^{\circ}C$ $V_R = 80V$			200	μΑ
V _F *	$T_j = 25^{\circ}C$ $I_F = 10mA$			0.32	V
	$T_j = 25^{\circ}C$ $I_F = 100mA$			0.42	
	$T_j = 25^{\circ}C$ $I_F = 1A$			1	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _j = 25°C	f = 1MHz	$V_R = 0V$		120		pF
			$V_R = 5V$		35		

* Pulse test: $t_p\!\le\!300\mu s~\delta\!<\!2\%$.

I_F (mA) 10³ 102 10 = 100 °C Тj í = 25 °C Tj. °C -55 -Тj 10-1 (V) ۷F 10-2 0 0.2 0.4 0.6 0.8

Figure 1. Forward current versus forward voltage at low level (typical values).

Figure 3. Reverse current versus junction temperature.



Figure 2. Forward current versus forward voltage at high level (typical values).



Figure 4. Reverse current versus V_{RRM} in per cent.



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Figure 5. Capacitance C versus reverse applied voltage V_{R} (typical values).



Figure 6. Surge non repetitive forward current for a rectangular pulse with t \leq 10 ms.



Figure 7. - Surge non repetitive forward current versus number of cycles.





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PACKAGE MECHANICAL DATA

MELF Glass



	DIMENSIONS						
REF.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	4.80		5.20	0.189		0.205	
ØB	2.50		2.65	0.098		0.104	
С	0.45		0.60	0.018		0.024	
ØD		2.50			0.098		

Δ7/

FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end. Weight: 0.15g

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